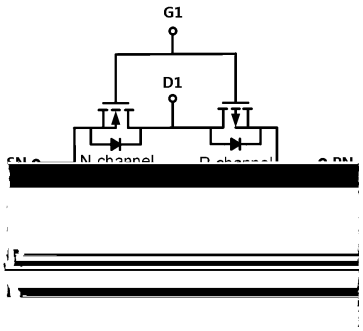
SOT23-6

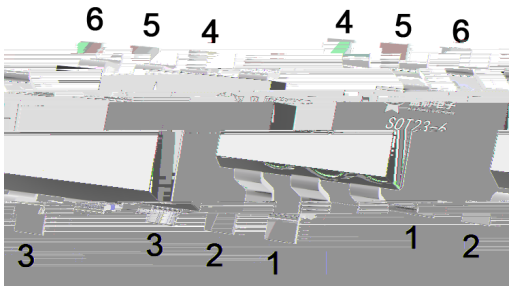
Complementary Enhancement MOSFET in a SOT23-6 Plastic Package.

N-channel	P-channel
V_{DS}(V)=30V	V_{DS}(V)=-30V
I_D=2.7A	I_D=-2.6A
$R_{DS(ON)}$@10V<80mΩ(TYP. 66 mΩ)	$R_{DS(ON)}$@-10V<95 mΩ(TYP. 75 mΩ)
$R_{DS(ON)}$@4.5V<130mΩ(TYP. 95 mΩ)	$R_{DS(ON)}$@-4.5V<150 mΩ(TYP. 88 mΩ)
HF Product.	

PWM

PWM applications,Load switch.



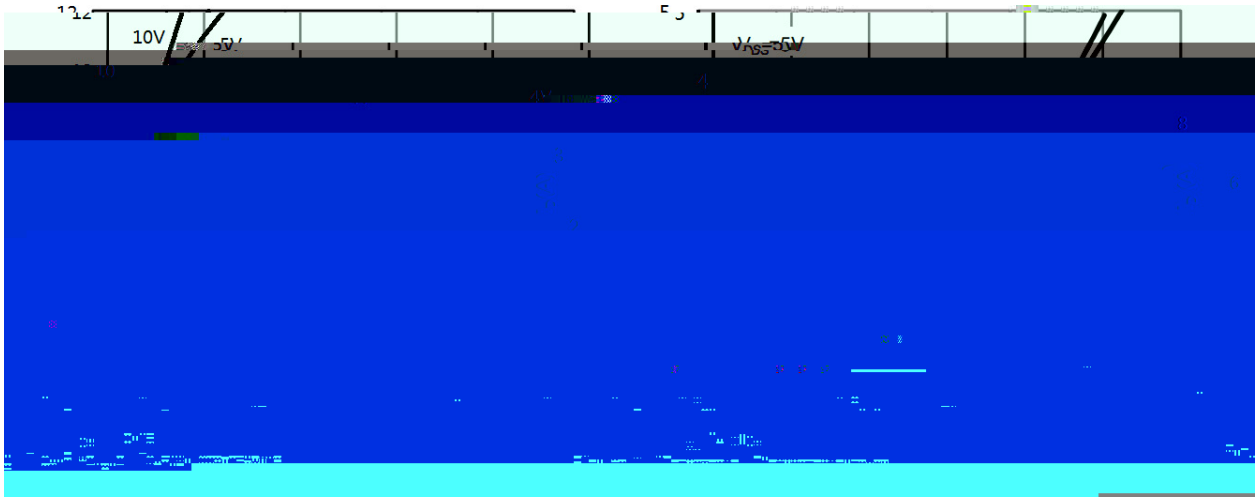


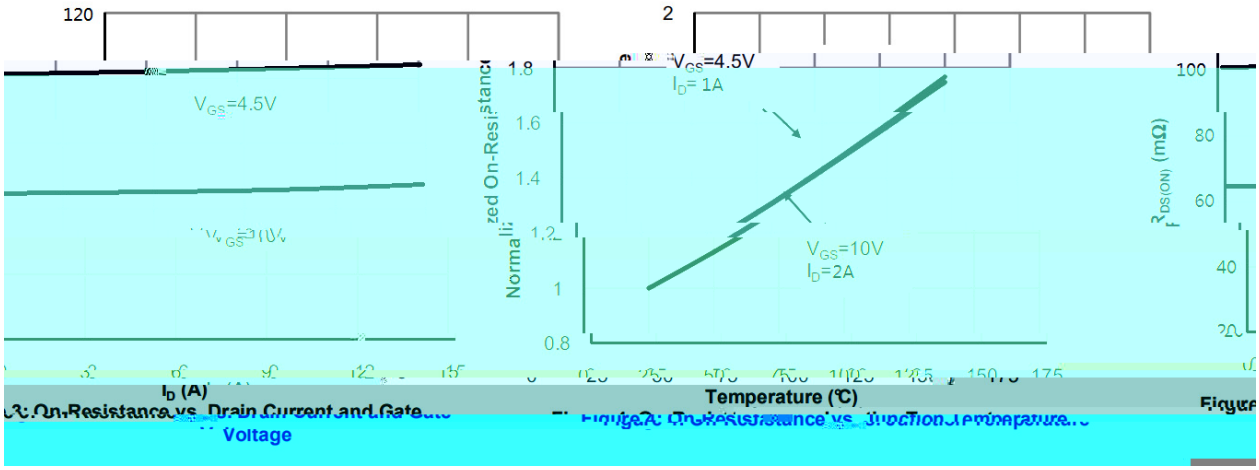
PIN1	G1	PIN 2	SN	PIN 3	G2
PIN 4	D2	PIN 5	SP	PIN 6	D1

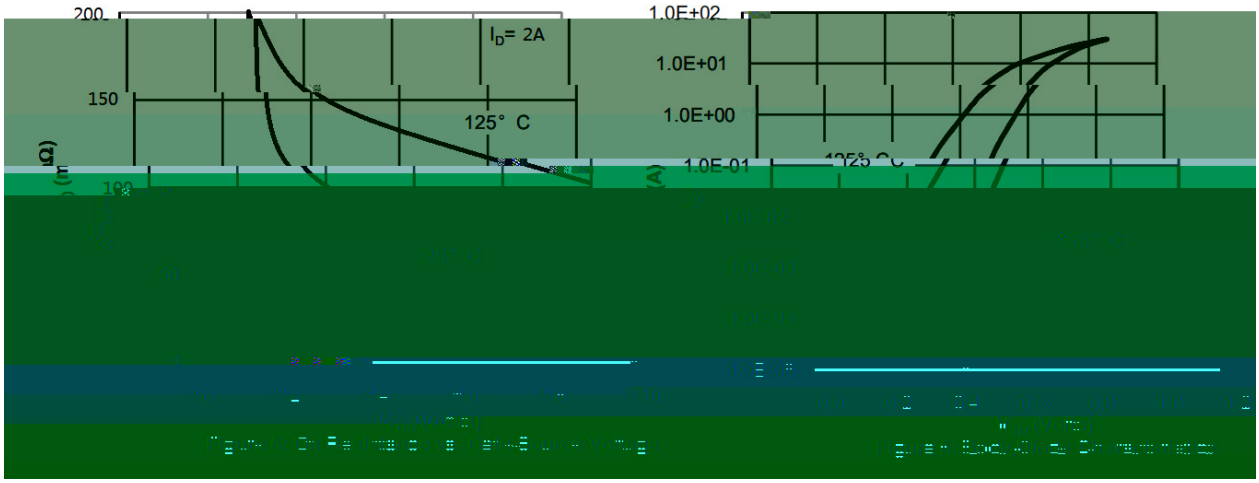
See Marking Instructions.

Parameter	Symbol	Rating		Unit
		N-channe	P-channell	
Drain-Source Voltage	V_{DSS}	30	-30	V
Gate-Source Voltage	V_{GSS}	±20		V
Continuous Drain Current	I_D	2.7	-2.6	A
Pulsed Drain Current	I_{DM}	7	-7	A
Power Dissipation	P_D	1		W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to +150		
Maximum Junction-to-Ambient	$R_{\theta JA}$	125		/W

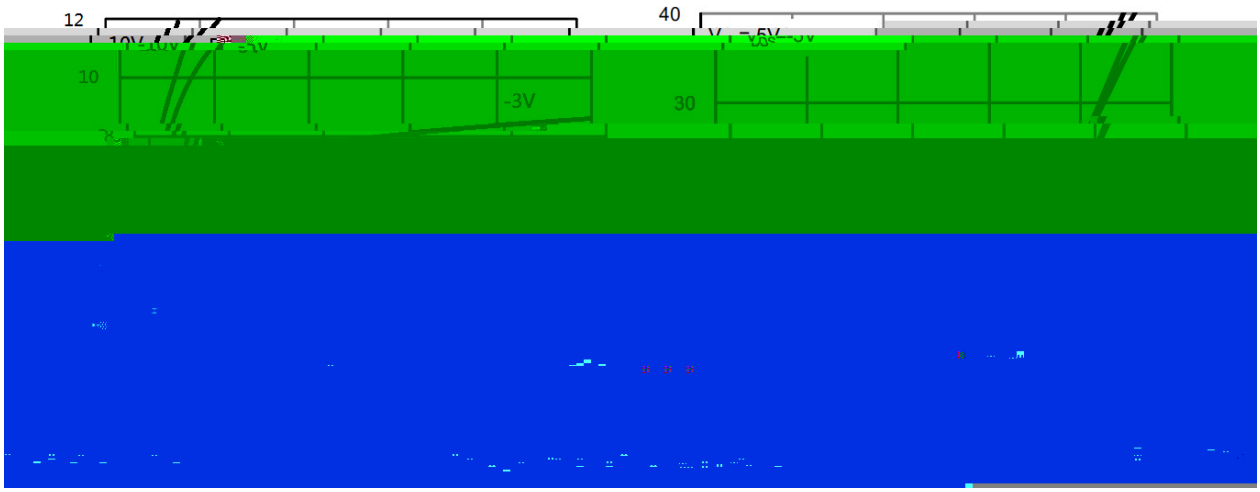
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	BV_{DSS}	V_{GS}=0	I_D=250μA	30	31.5		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0	V_{DS}=24V			1.0	μA
Gate–Body Leakage.	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			±100	nA
Static Drain–Source On–Resistance	$R_{DS(on)1}$	V_{GS}=10V	I_D=2.0A		66	80	mΩ
	$R_{DS(on)2}$	V_{GS}=4.5V	I_D=1.0A		95	130	mΩ
Drain–Source Diode Forward Voltage	V_{SD}	V_{GS}=0V	I_D=1.0A			1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250μA	1.0	1.45	2.0	V
Input Capacitance	C_{iss}	V_{DS}=15V f=1.0MHz	V_{GS}=0V		200		pF
Output Capacitance	C_{oss}				30		pF
Reverse Transfer Capacitance	C_{rss}				20		pF
Total Gate Charge	Q_g	V_{GS}=10V, I_D=2A	V_{DS}=15V		5		nC
Gate Source Charge	Q_{gs}				0.8		
Gate Drain Charge	Q_{gd}				1.7		

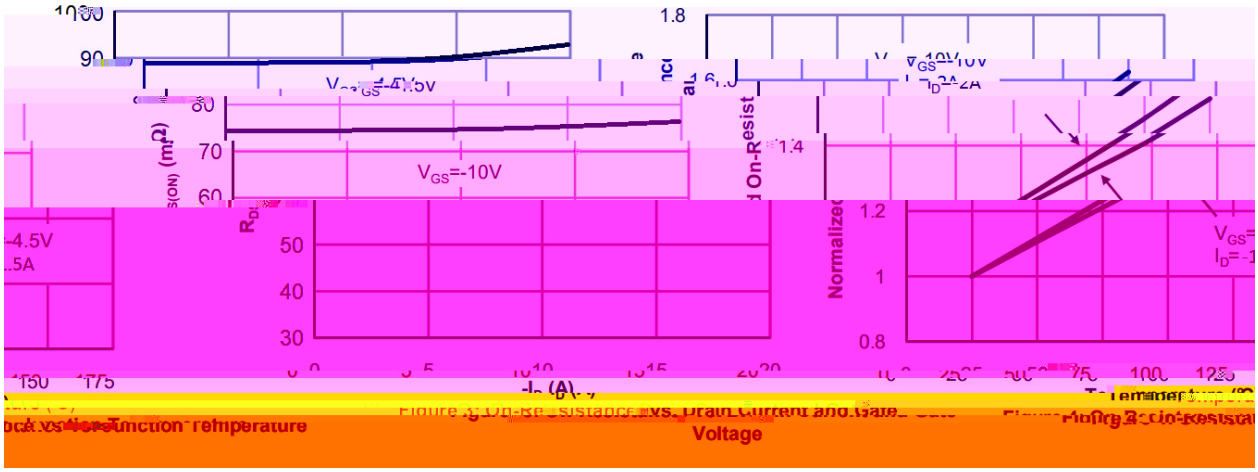

10V
5V
V_{GS}=5V

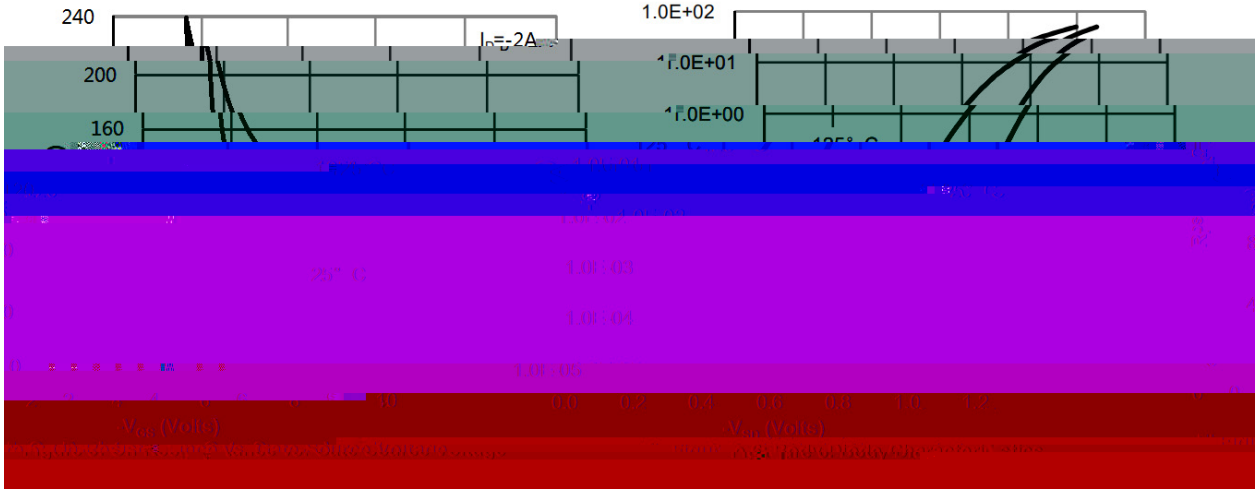

120
V_{GS}=4.5V
V_{GS}=10V
I_D (A)
Voltage
2
V_{GS}=4.5V
I_D= 1A
V_{GS}=10V
I_D=2A
Temperature (℃)
100
80
60
40
1.8
1.6
1.4
1.2
1
0.8

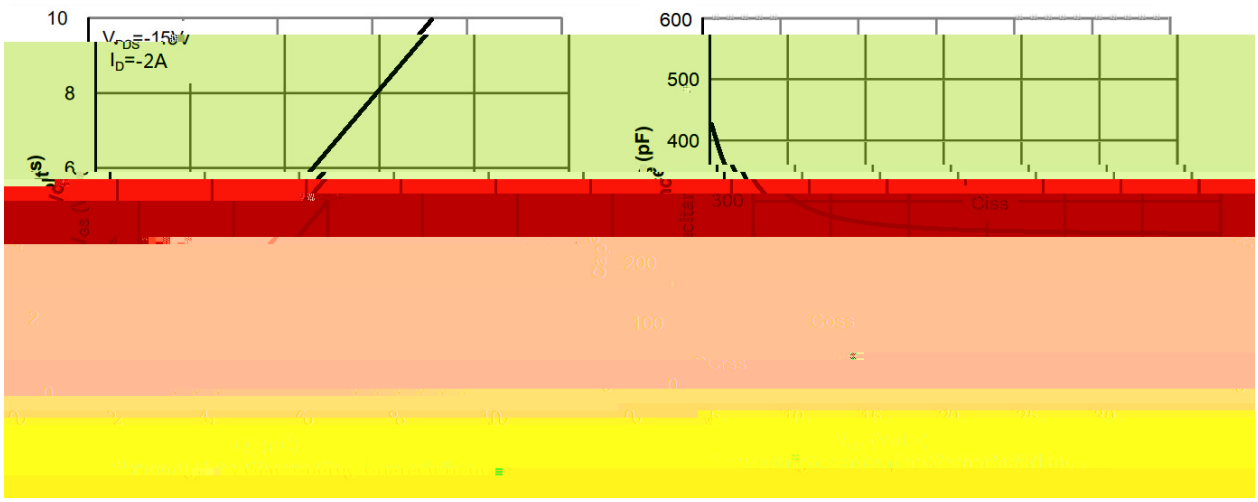

200
150
I_D= 2A
125° C
1.0E+02
1.0E+01
1.0E+00
1.0E-01

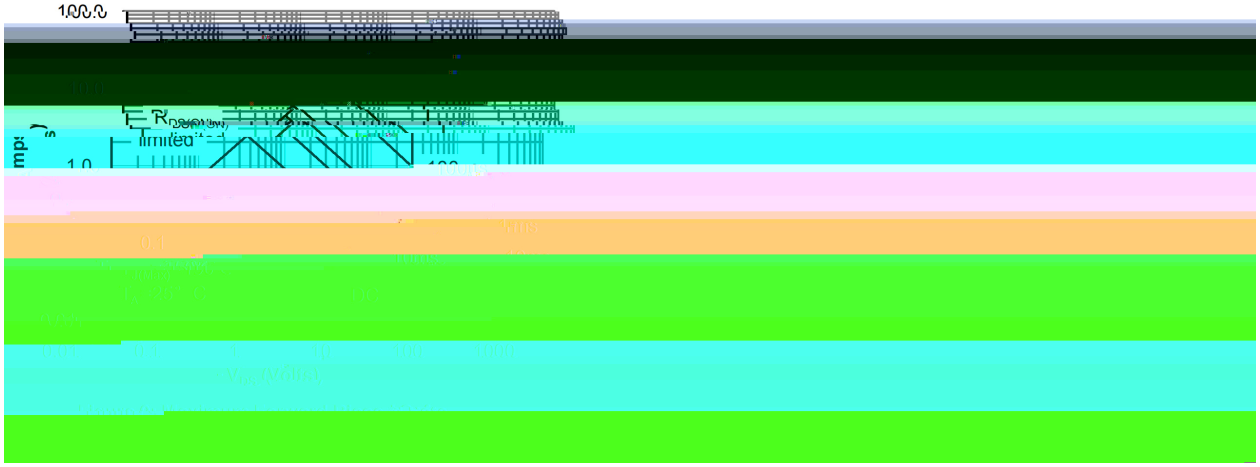
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V I_D=-250μA	-30	-31.5		V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-0.5	-0.85	-2.0	V
Static Drain–Source On–Resistance	$R_{DS(on)}$	V_{GS}=-10V I_D=-2 A		75	95	mΩ

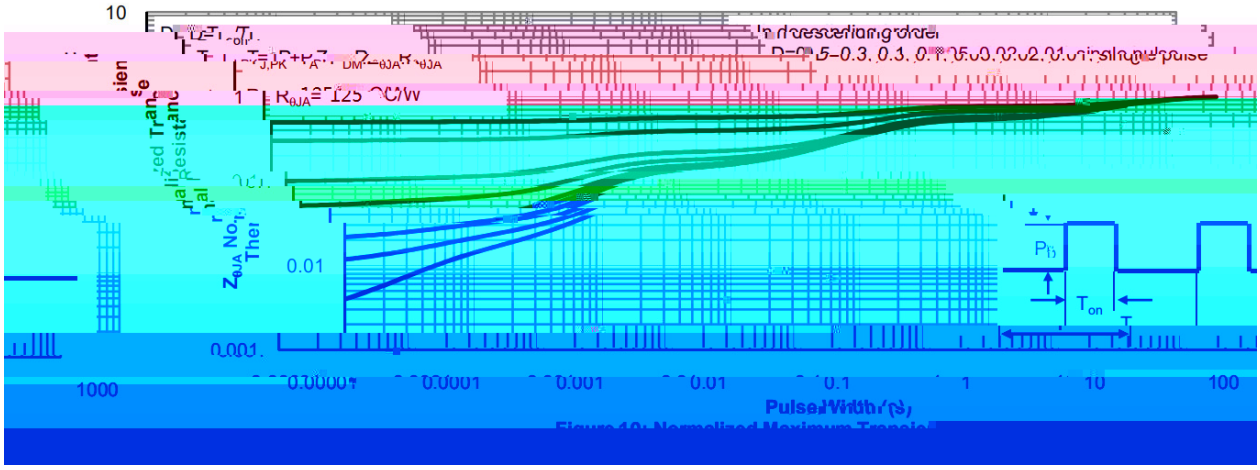

12
10
-3V
40
30

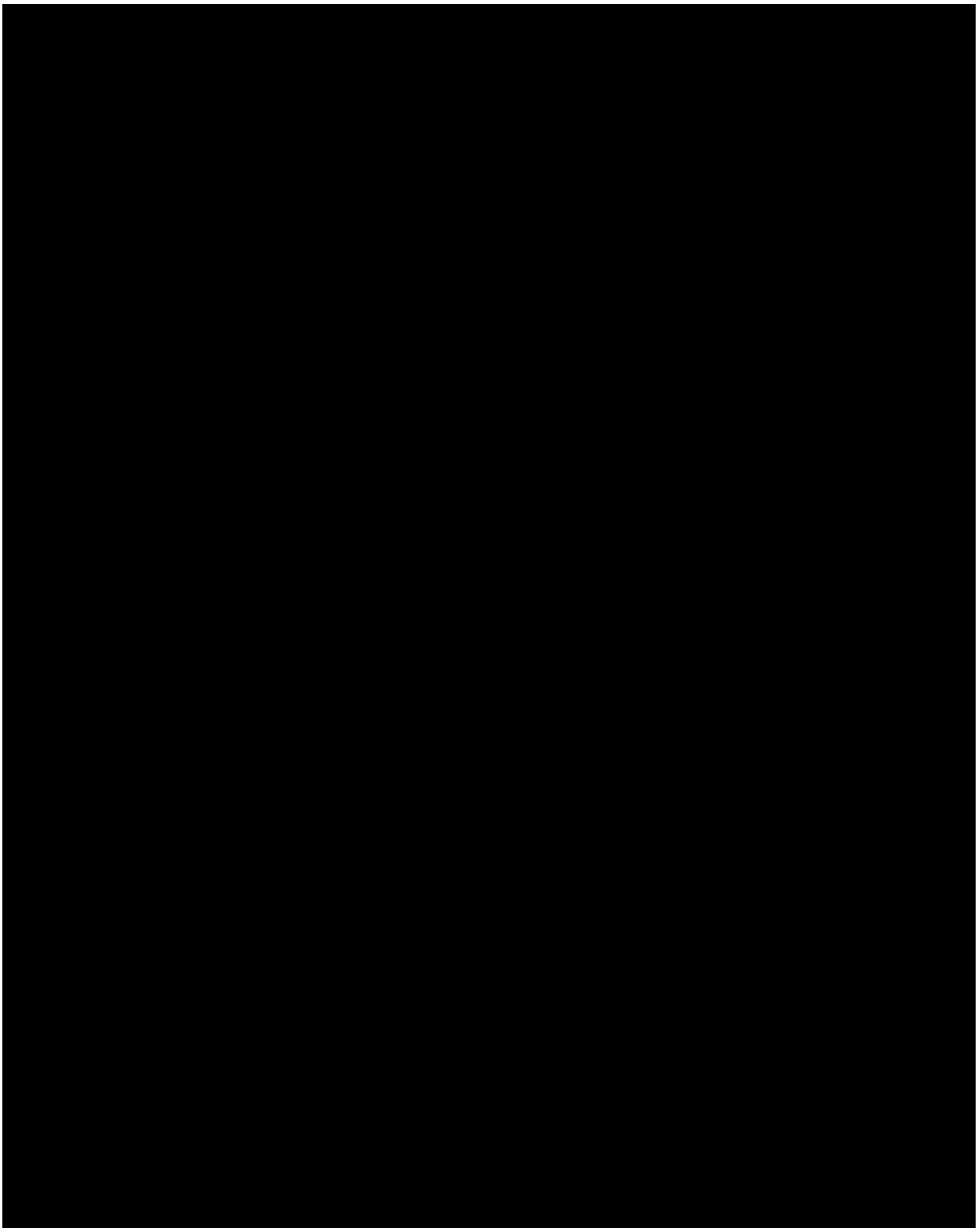

90
80
70
60
50
40
30
V_{GS}=-10V
1.8
1.4
1.2
1
0.8
Normalized
Voltage

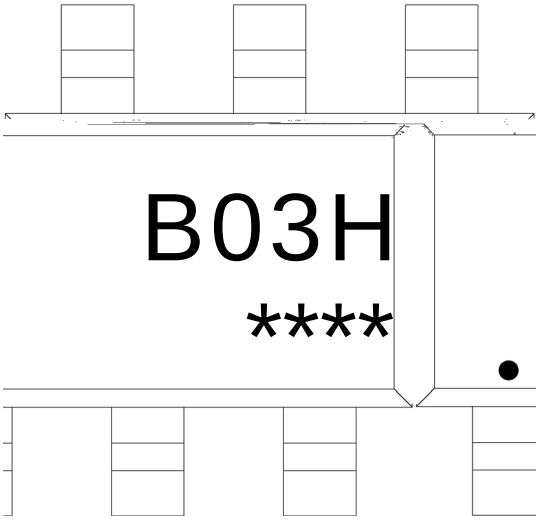

240
200
160
I_D=-2A
1.0E+02
1.0E+01
1.0E+00


10
8
6
600
500
400
300
200
100
0
Ciss
Coss
Crss


Limited
1ms
10ms


10
0.01
0.001
1000
0.0001
0.001
0.01
0.1
1
10
100
Ton





B03:

H

****:

Note:

B03	Product Type Code
H	Company Code
****:	Lot No.Code,code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)



				Note:
1	150	180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5		5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3				